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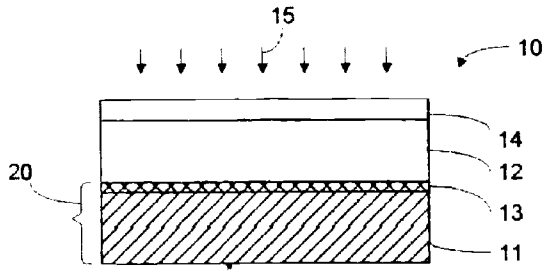



Figure 1

(57) Abstract: A method of forming a doped Group IBIIIAVIA absorber layer for solar cells by reacting a a metallic precursor layer with a dopant structure. The metallic precursor layer including Group IB and Group HIA materials such as Cu, Ga and In are deposited on a base. The dopant structure is formed on the metallic precursor layer, wherein the dopant structure includes a stack of one or more Group VIA material layers such as Se layers and one or more a dopant material layers such as Na.

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